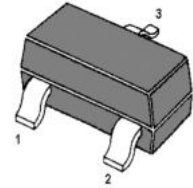


Features

- Silicon epitaxial planar transistors
- For switching and amplifier applications



1.BASE 2.EMITTER 3.COLLECTOR
SOT-23 Plastic Package

Absolute Maximum Ratings (T_a = 25°C)

Parameter	Symbol	Value	Unit
Collector Base Voltage	-V _{CBO}	50	V
Collector Emitter Voltage	-V _{CEO}	45	V
Emitter Base Voltage	-V _{EBO}	5	V
Collector Current	-I _C	500	mA
Power Dissipation	P _{tot}	300	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	- 55 to + 150	°C

Characteristics at T_a = 25°C

Parameter	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at -V _{CE} = 1 V, -I _C = 100 mA	- RND BC817-16	h _{FE}	100	-	250	-
	- RND BC817-40	h _{FE}	250	-	600	-
		h _{FE}	40	-	-	-
at -V _{CE} = 1 V, -I _C = 500 mA						
Collector Base Cutoff Current at -V _{CB} = 20 V	C _{cbo}	-	5	-	pF	
Emitter Base Cutoff Current at -V _{EB} = 5 V	-I _{EBO}	-	-	100	nA	
Collector Base Capacitance at -V _{CB} = 10 V, f = 1 MHz	-V _{(BR)CEO}	45	-	-	V	
Collector Emitter Saturation Voltage at -I _C = 500 mA, -I _B = 50 mA	-V _{CE(sat)}	-	-	0.7	V	
Base Emitter Voltage at -I _C = 500 mA, -V _{CE} = 1 V	-V _{BE(on)}	-	-	1.2	V	
Transition Frequency at -V _{CE} = 5 V, -I _C = 10 mA, f = 50 MHz	f _T	100	-	-	MHz	

